

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3167816	memory or storage	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/18 17:27
L2	64598	1 and (cell or element) with amplif\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/18 17:28
L3	72	2 and (voltage or potential or level) near3 regulat\$5 with (bipolar or npn or pnp)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/18 17:30
L4	11	2 and (voltage or potential or level) near3 regulat\$5 with (bipolar or npn or pnp) with positive	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/18 17:34
L5	18	3 and (voltage or potential or level) near3 regulat\$5 with (bipolar or npn or pnp) with amplif\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/18 17:40
L6	2	1 and (bipolar or npn or pnp) with (substrate or wafer) with access near3 transistor with regulat\$5 with (voltage or potential or level)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/18 17:43
L7	3	1 and (bipolar or npn or pnp) with (substrate or wafer) with (isolat\$5 or separat\$5) with transistor with regulat\$5 with (voltage or potential or level)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/18 17:46